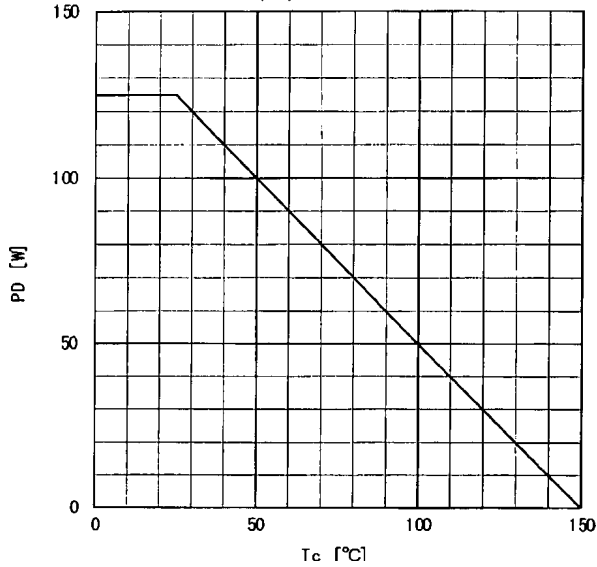
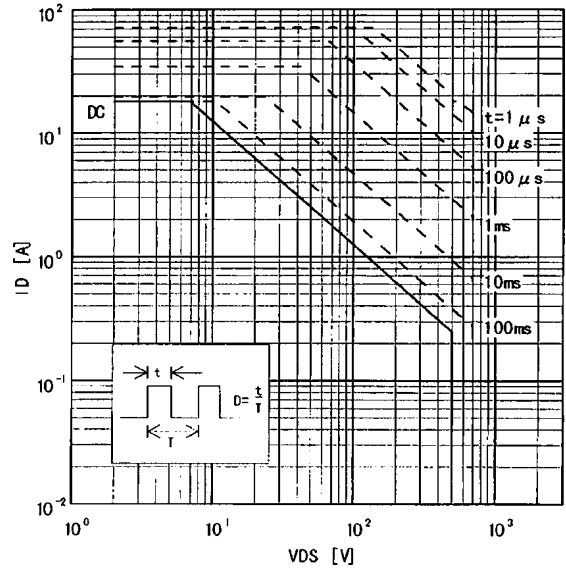


Characteristics

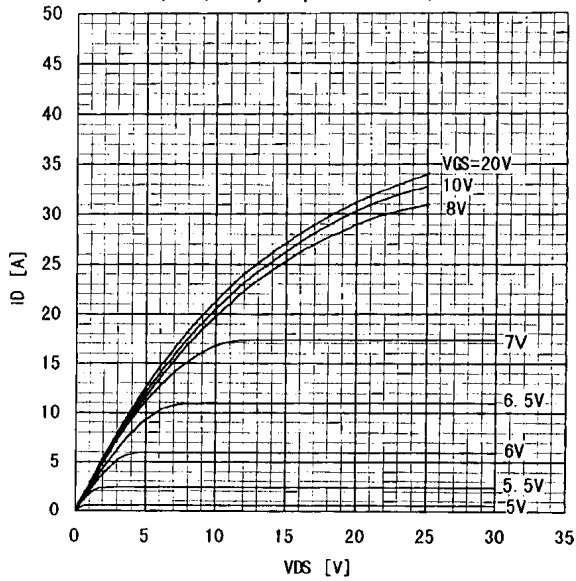
Power Dissipation
 $PD=f(T_c)$



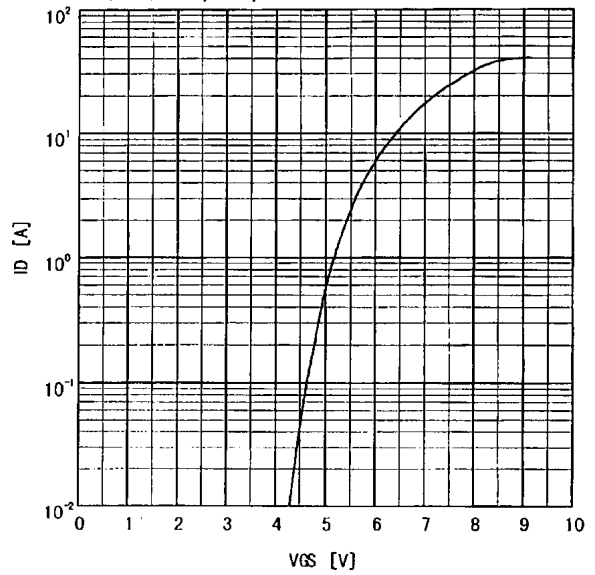
Safe operating area
 $ID=f(V_{DS}) : D=0.01, T_c=25^\circ C$



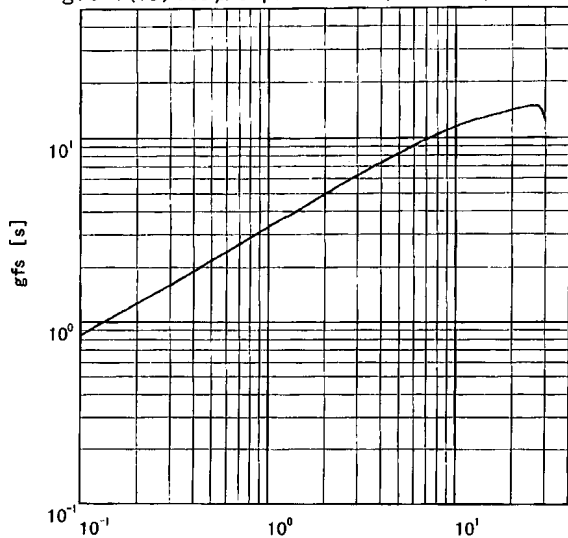
Typical output characteristics
 $ID=f(V_{DS}) : 80 \mu s$ pulse test, $T_c=25^\circ C$



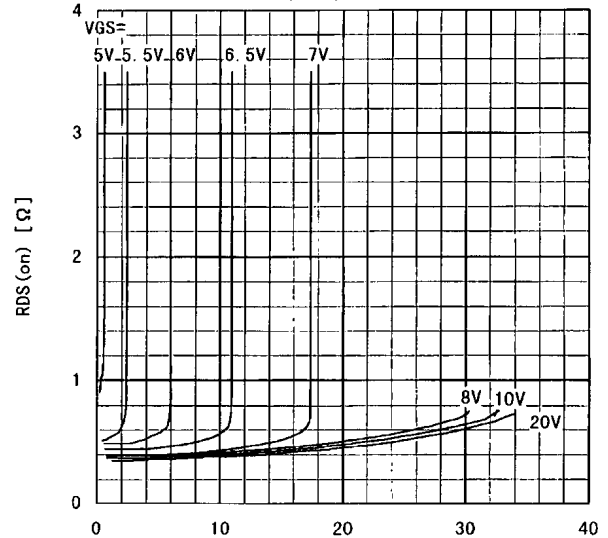
Typical transfer characteristic
 $ID=f(V_{GS}) : 80 \mu s$ pulse test, $V_{DS}=25V, T_{ch}=25^\circ C$



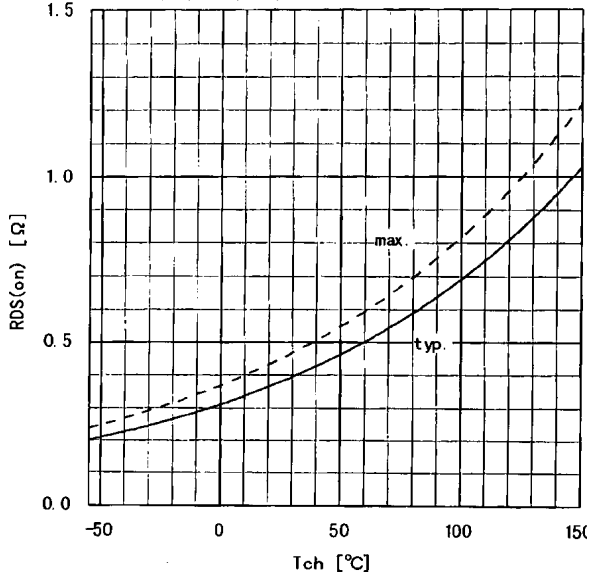
Typical forward transconductance
 $g_{fs}=f(I_D) : 80 \mu s$ pulse test, $V_{DS}=25V, T_{ch}=25^\circ C$



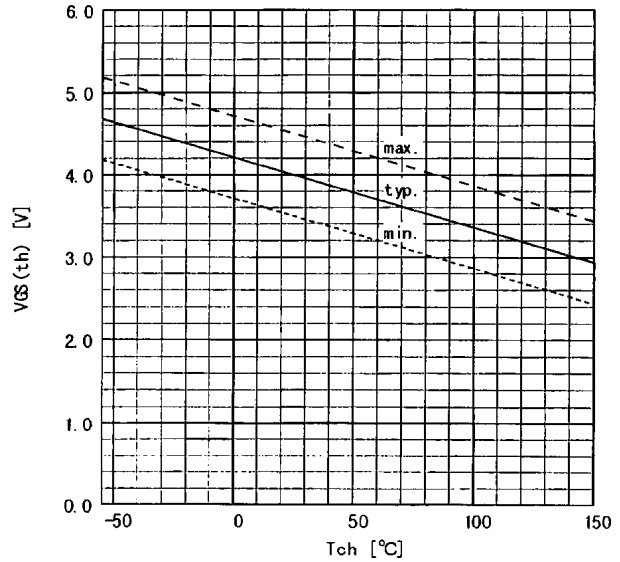
Typical drain-source on-state resistance
 $R_{DS(on)}=f(I_D) : 80 \mu s$ pulse test, $T_c=25^\circ C$



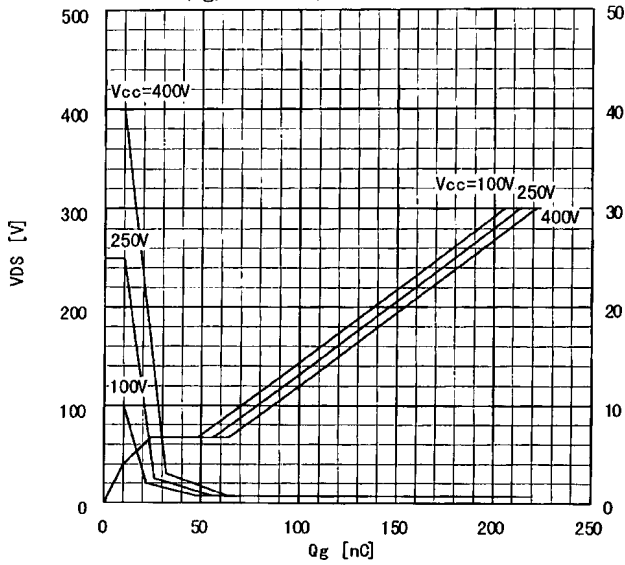
Drain-source on-state resistance
 $R_{DS(on)} = f(T_{ch}) : I_D = 9A, V_{GS} = 10V$



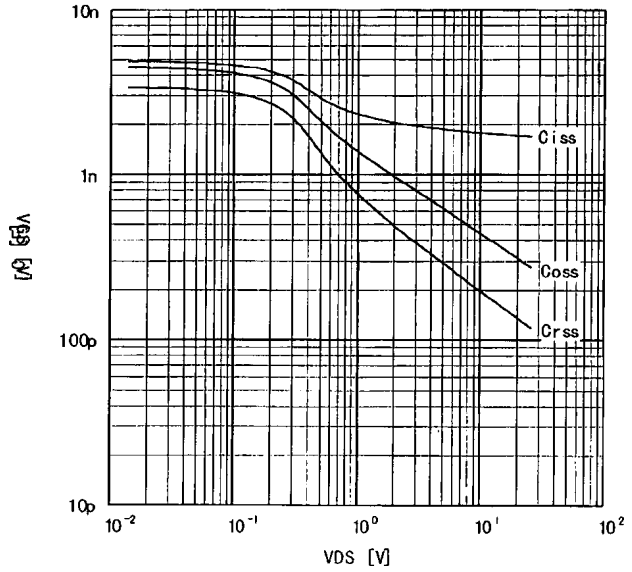
Gate threshold voltage
 $V_{GS(th)} = f(T_{ch}) : I_D = 1mA, V_{DS} = V_{GS}$



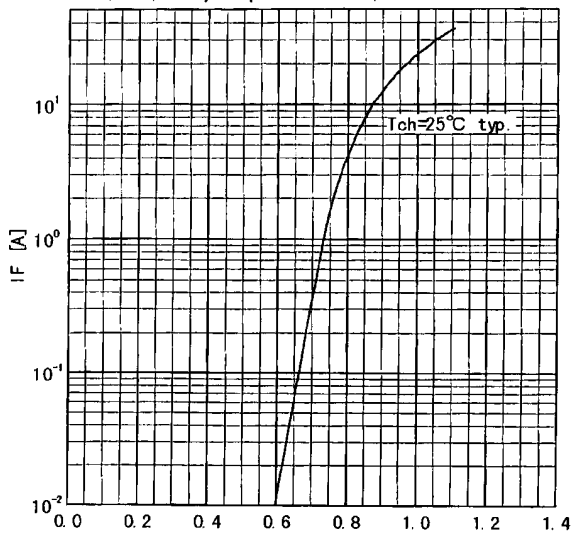
Typical gate charge characteristic
 $V_{GS} = f(Q_g) : I_D = 18A, T_c = 25°C$



Typical capacitances
 $C = f(V_{DS}) : V_{GS} = 0V, f = 1MHz$



Forward characteristic of reverse of diode
 $I_F = f(V_{SD}) : 80 \mu s \text{ pulses test}, V_{GS} = 0V$



Avalanche energy derating
 $E_{as} = f(\text{starting } T_{ch}) : V_{CC} = 50V, I_{AV} = 18A$

